

RJK5002DPD

500V - 2.4A - MOS FET High Speed Power Switching

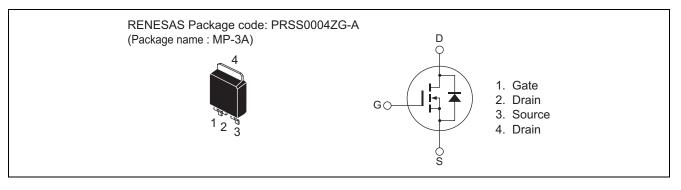
Aug 08, 2012

Datasheet

Features

- Low on-state resistance $R_{DS(on)} = 3.83 \ \Omega$ typ. (at $I_D = 1.2 \ A$, $V_{GS} = 10 \ V$, $Ta = 25^{\circ}C$)
- High speed switching
- Then speed switching

Outline



Absolute Maximum Ratings

			(Ta = 25°C)
Item	Symbol	Value	Unit
Drain to source voltage	V _{DSS}	500	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	ID Note1	2.4	А
Drain peak current	I _{D(pulse)} Note2	4.8	А
Body-drain diode reverse drain current	I _{DR} ^{Note1}	2.4	А
Body-drain diode reverse drain peak current	I _{DR(pulse)} Note2	4.8	А
Avalanche current	I _{AP} ^{Note3}	2.4	A
Channel dissipation	Pch Note4	30	W
Channel to case thermal Impedance	θch-c	4.17	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. Limited by Tch max.

2. Pulse width limited by safe operating area.

2. STch = 25° C, Tch $\leq 150^{\circ}$ C

4. Value at $Tc = 25^{\circ}C$



Electrical Characteristics

						$(Ta = 25^{\circ}C)$
ltem	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown	V _{(BR)DSS}	500	—	—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
voltage						
Zero gate voltage drain current	I _{DSS}	—	—	1	μΑ	$V_{DS} = 500 \text{ V}, V_{GS} = 0$
Gate to source leak current	I _{GSS}	—	—	±0.1	μΑ	$V_{GS}=\pm 30~V,~V_{DS}=0$
Gate to source cutoff voltage	V _{GS(off)}	3.5	_	4.5	V	$V_{DS} = 10 V, I_D = 1 mA$
Static drain to source on state resistance	R _{DS(on)}	—	3.83	5.00	Ω	$I_D = 1.2 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note5}}$
Input capacitance	Ciss	_	165	—	pF	V _{DS} = 25 V
Output capacitance	Coss	_	21	—	pF	V _{GS} = 0 f = 1 MHz
Reverse transfer capacitance	Crss	_	2.6	—	pF	
Turn-on delay time	t _{d(on)}		11	—	ns	I _D = 1.2 A
Rise time	tr		12	—	ns	$V_{GS} = 10 V$ $R_L = 208 \Omega$ $Rg = 10 \Omega$
Turn-off delay time	t _{d(off)}	—	22	—	ns	
Fall time	t _f	—	22	—	ns	
Total gate charge	Qg	—	6.7	—	nC	V _{DD} = 400 V
Gate to source charge	Qgs	—	1.3	—	nC	V _{GS} = 10 V I _D = 2.4 A
Gate to drain charge	Qgd	—	3.8	—	nC	
Body-drain diode forward voltage	V _{DF}	—	0.9	1.5	V	$I_F = 2.4 \text{ A}, V_{GS} = 0^{Note5}$
Body-drain diode reverse recovery	t _{rr}	_	235	_	ns	$I_F = 2.4 \text{ A}, V_{GS} = 0$
time						V _{DD} = 400 V
						di _F /dt = 100 A/µs

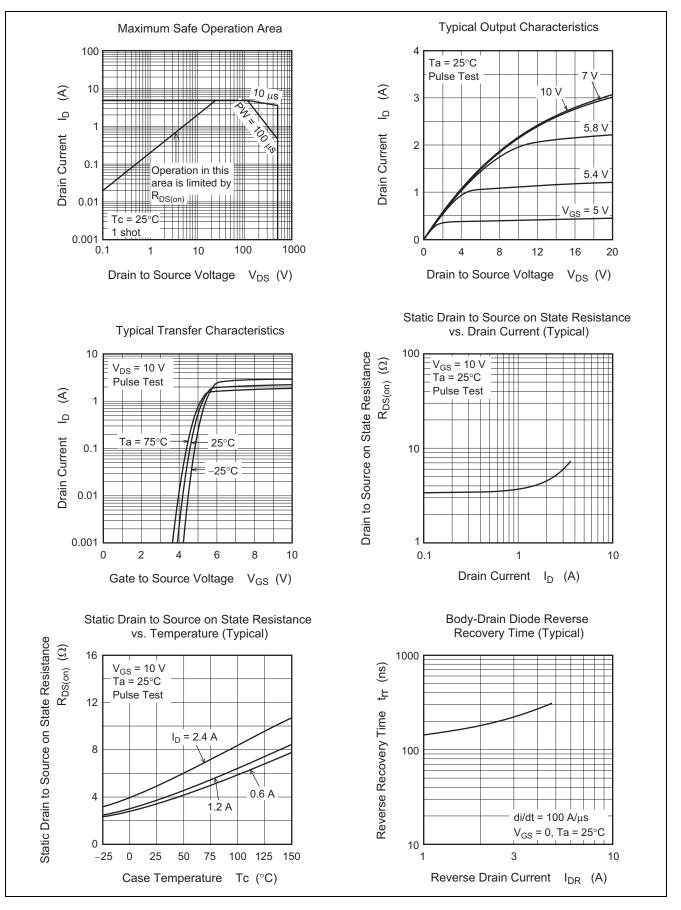
Note: 5. Pulse test

6. Since this device is equipped with high voltage FET chip ($V_{DSS} \ge 500 \text{ V}$), high voltage may be supplied. Therefore, please be sure to confirm about electric discharge between drain terminal and other terminal.

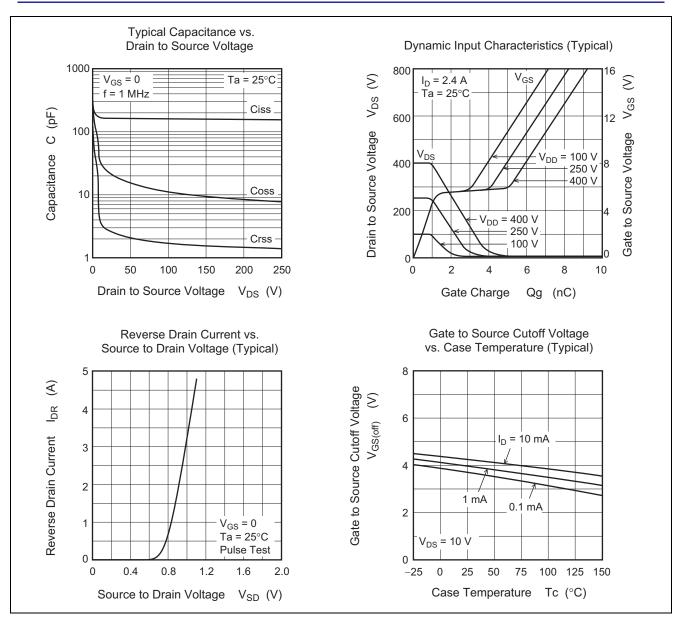
This device is sensitive to electrostatic discharge.
It is recommended to adopt appropriate cautions when handling this product.



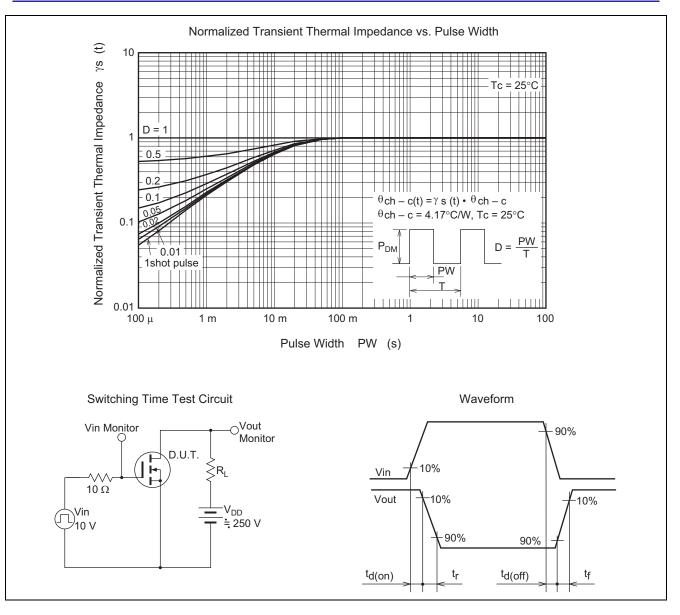
Main Characteristics





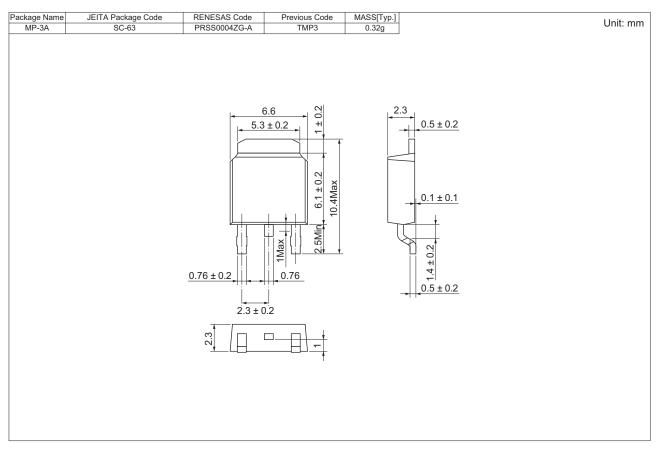








Package Dimensions



Ordering Information

Orderable Part No.	Quantity	Shipping Container
RJK5002DPD-00#J2	3000 pcs	Taping



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